



Scientific council
27/06/2023



The core-facility C4Pi

for the development of CMOS-MAPS

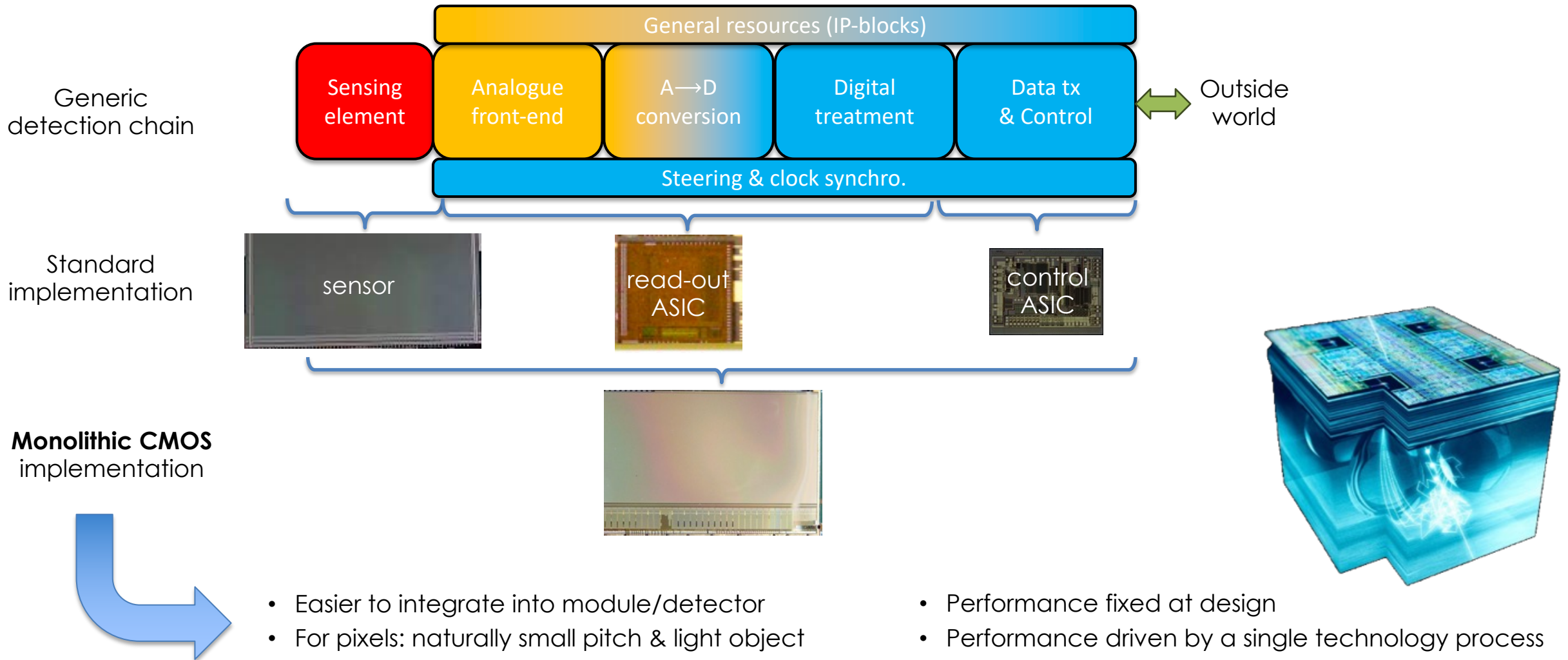
- Missions & expertise
- Team, equipment & network
- Technologies
- Internal technological R&D



Université

de Strasbourg

Monolithic Active Pixel Sensor in CMOS technology

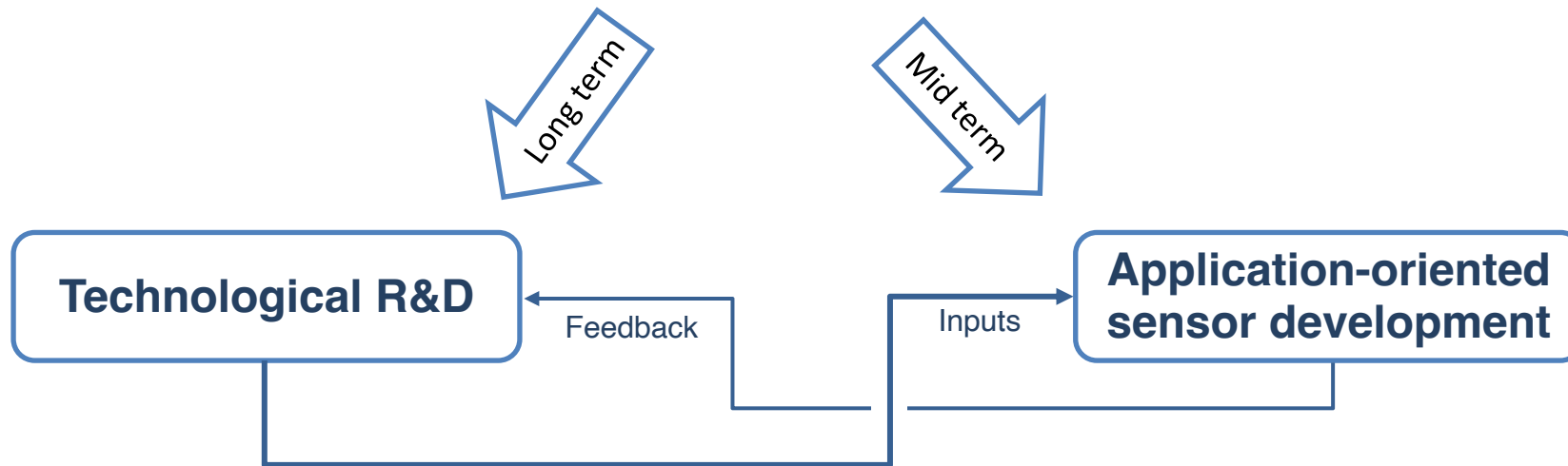


- Easier to integrate into module/detector
- For pixels: naturally small pitch & light object

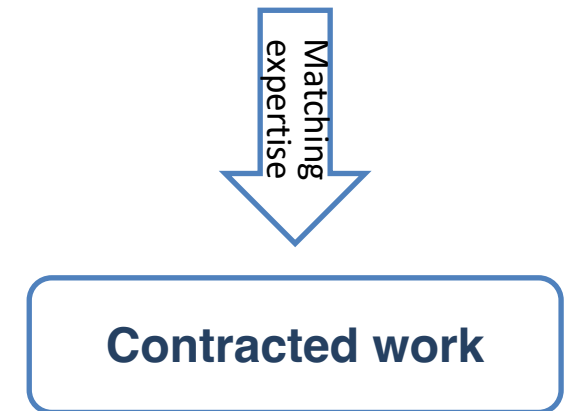
- Performance fixed at design
- Performance driven by a single technology process

C4Pi facility born end of 2019, acknowledging specialisation of micro-electronic group in CMOS-MAPS

Requests from scientific groups

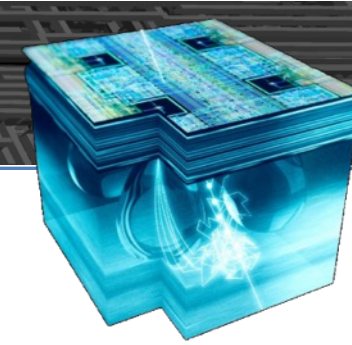


Requests from users
(lab or company)

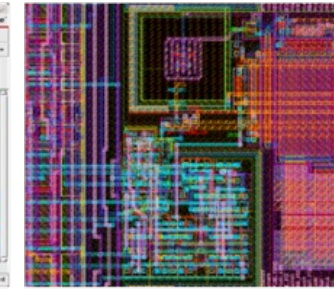
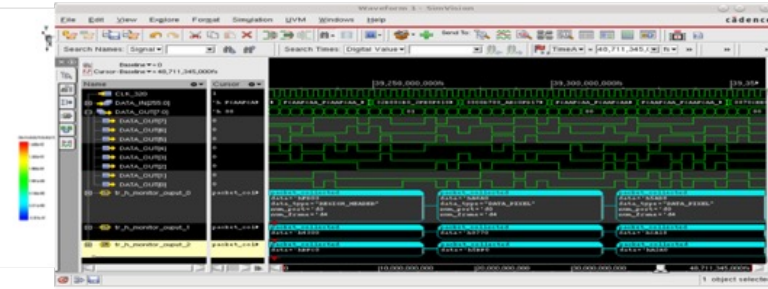
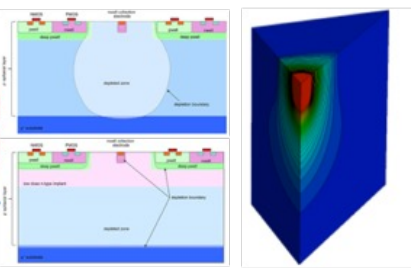
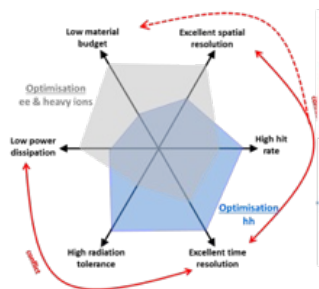


Instrumental
knowledge

Science!



C4Pi covers the complete range of techniques required for MAPS developments

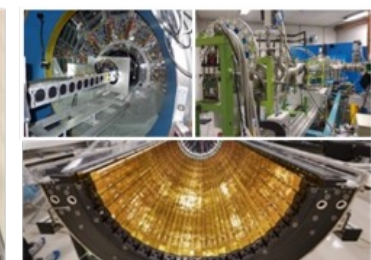
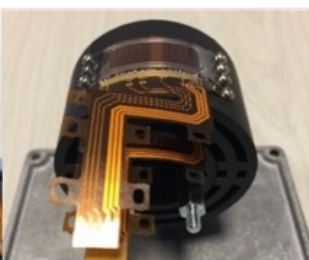
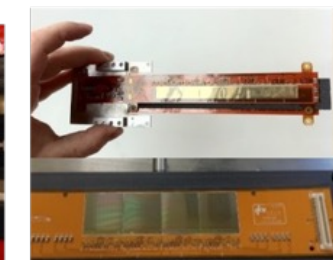
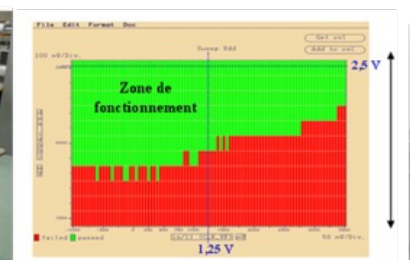


Requirements

Charge collection

Front-End (analog+digital) / Functional blocs / Syst. architecture

Fab interface



DAQ development & Tests

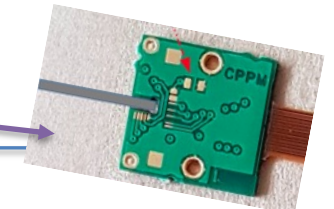
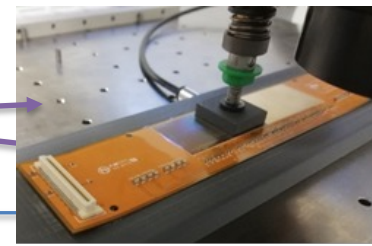
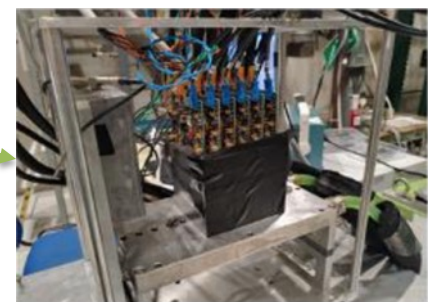
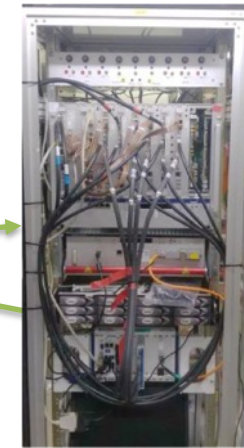
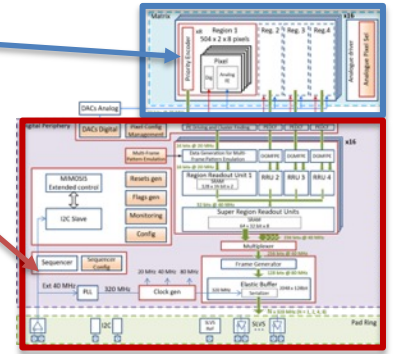
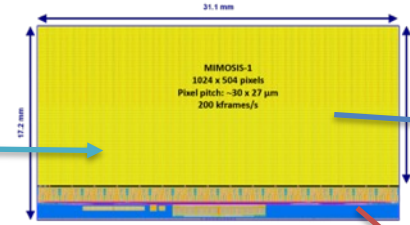
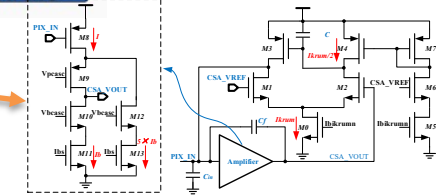
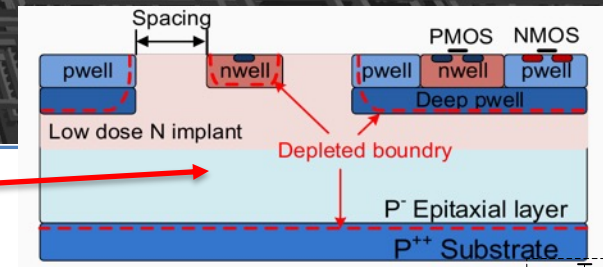
Integration

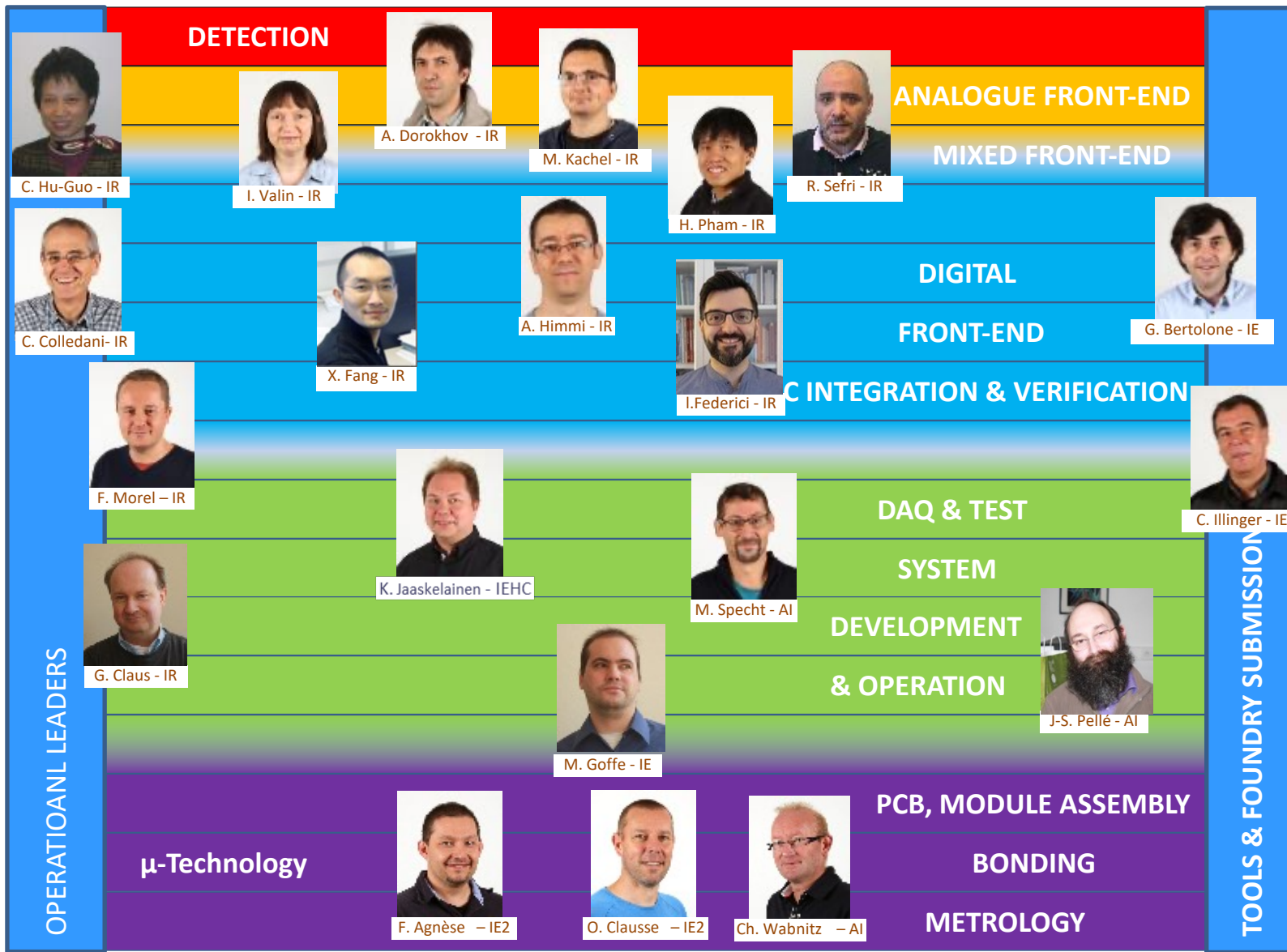
Construction Installation

Expertise

Sensitive layer	Collection node	
In-pixel analogue front-end	Bias monitoring	
Digital conversion	Digitisation	
Digital front-end & back-end	Read-out architecture	
Register Transfer Level	Top description	
Integration	Synthesis, Layout	
Design Rule Checking	Verification	
IP, component creation	Fabrication	
Test systems prototyping	DAQ, Control, data transfert systems design	
Board, flex, detection module design		
Hardware / Firmware / Software design	Test setup intergration	
IP validation	Functional tests	Physical characterisation
Laboratory tests	Beam tests	Production tests
Board/flex component population		tool design
ASIC/wafer probe testing		Module validation
Manual/automatic assembly	Bonding	2D/3D Metrology

TOOLS & Foundry support





- PhD students**



J. Soudier – Doc2



C. Lemoine (CERN) – Doc1

+2 positions starting in 2023

- Master students**

C. Anntony, G. Morel, N. Vergara – M2 microelectronics

N. Favriou – M2 physics

- Bachelor students**

M. Grau – L2 electronics

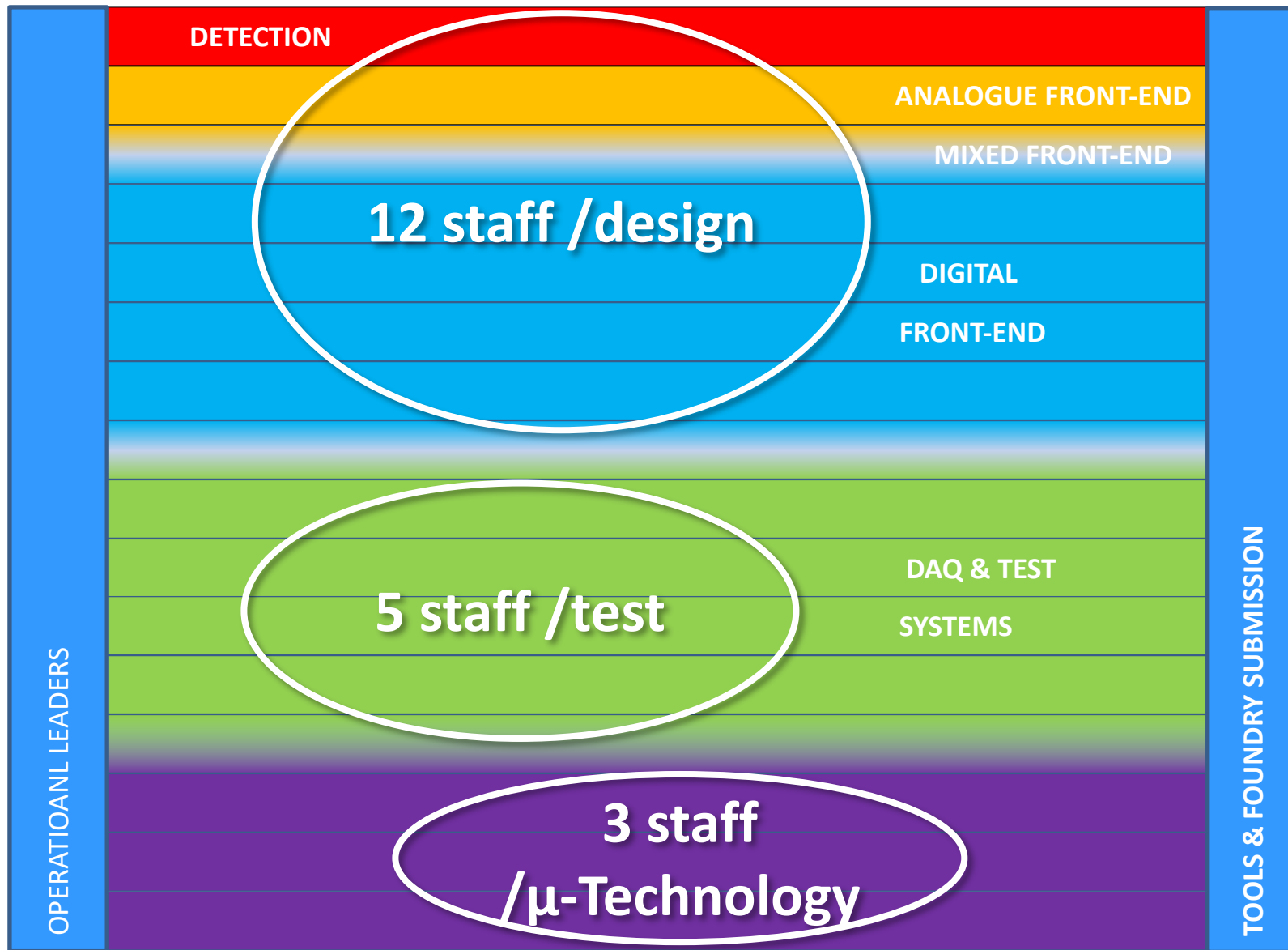
- Apprentices**



B. Faechtig – LPro1



T. Jacques – BUT3

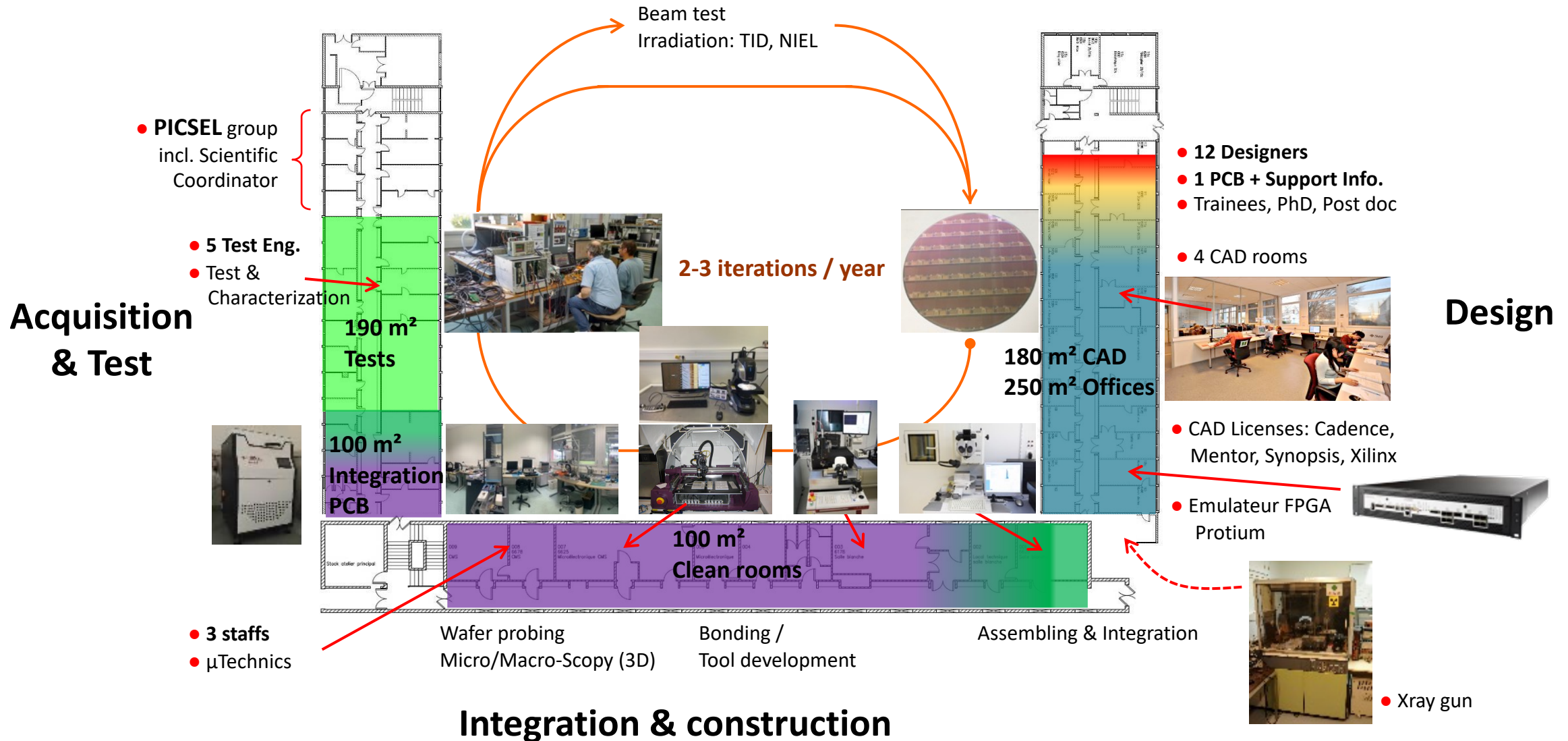


- Design work
 - ~4 FTE for large project
 - ~1.5 FTE for R&D (staff+student)
- => Expertise is shared among projects

- Mostly focused on MIMOSIS
- Evolution toward multi-projects

- Each staff specialised
- Participation of all to all projects

Equipment



■ Staff

- Expertise in bonding: 1 person
 - Used by all projects + strong point of contracted works

→ training plan for colleague + recruitment plan

■ CMOSS process

- Access to TPSCo 65 nm → Tower 180 nm in case of failure → Major international issue if 2nd failure

■ Equipment

- Bonding machine
 - Used by all projects + strong point of contracted works

→ 150 k€ in case of failure

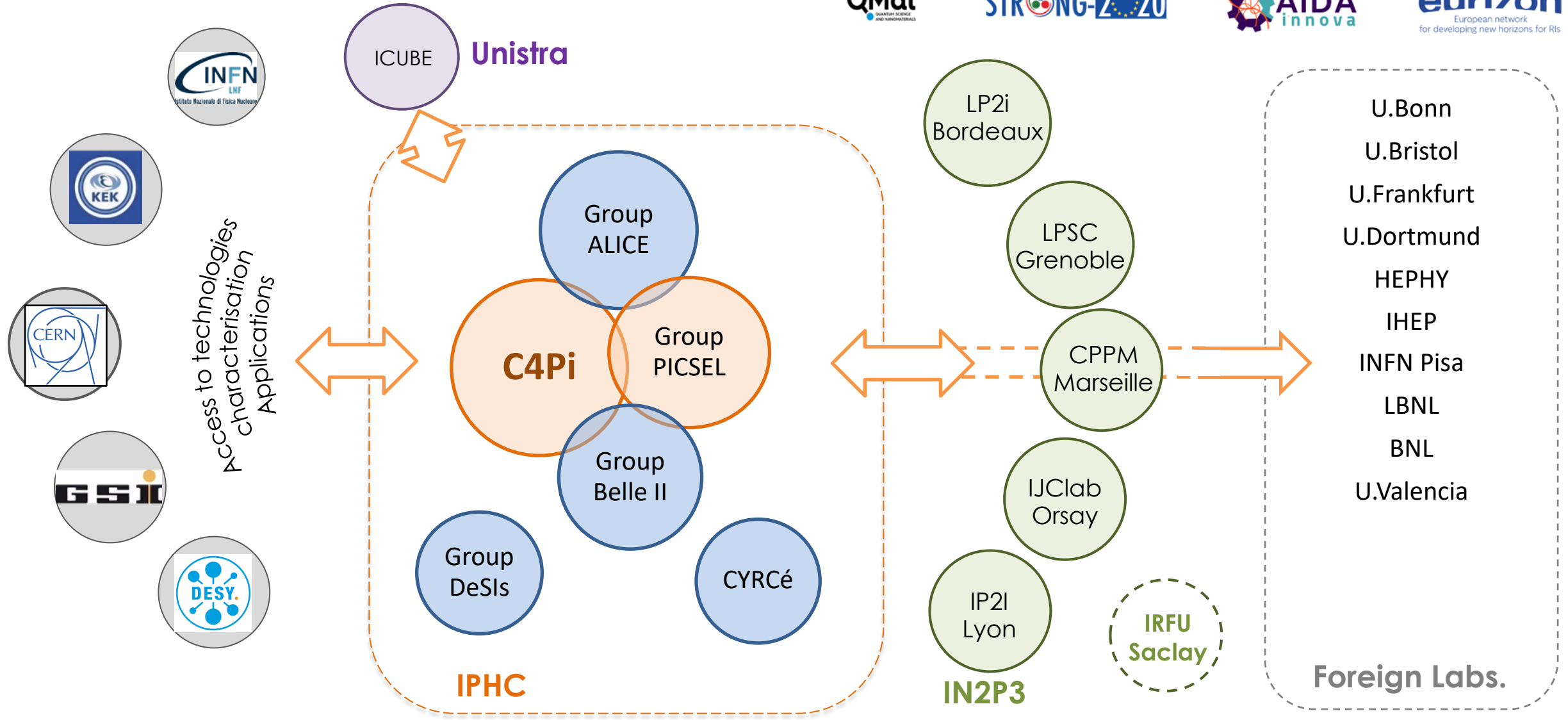
- Probe station too old for production & 12"
 - Important for MIMOSIS distribution (solution in Frankfurt)
 - Key for Belle II production (solutions with VTX partners)
 - Asset for R&D with TPSCo 65 nm

→ 350 k€ budget under planning

- Automatic placement machine
 - Key for Belle II production (solutions with VTX partners)

→ 150 k€ in case of failure

Network



- Maintaining access to processes costs resources → **limited nb of CMOS processes** handled at C4Pi
- C4Pi strategy: **mainstream processes** → fabrication robustness guaranteed

MIMOSA-1, 1999, AMS 600 nm

- AMS 350 nm

- **2004**-2011
- MIMOSA-26
- MIMOSA-28

- XFAB 350 nm

- ALPHABeast for DeSis 2022

- Tower 180 nm

- Since **2011**
- CE-18 + others for R&D
- ALPIDE for ALICE-ITS2
- MIMOSIS for CBM-MVD
- OBELIX-1 for Belle II-VTX
- TIIX for STRONG EU-project

- TPSCo 65 nm

- Since **2020**
- MOSS for ALICE-ITS3
- CE-65 series for R&D
- **Main choice for ECFA-DRDs**



Current processes

C4Pi proposal to ECFA-DRD7 for 180 nm contact-point (2024-27)

Scientific applications → R&D @ C4Pi with general trend = maximise CMOS-MAPS potential

- “internal” R&D = upstream advances (+ PhD / Master student)
- Not necessarily only internal

■ Amplification in silicon

- Low gain <10, get rid of analogue front-end
=> Reduce pixel pitch, reduce power dissipation, increase sensitivity

■ Read-out architecture

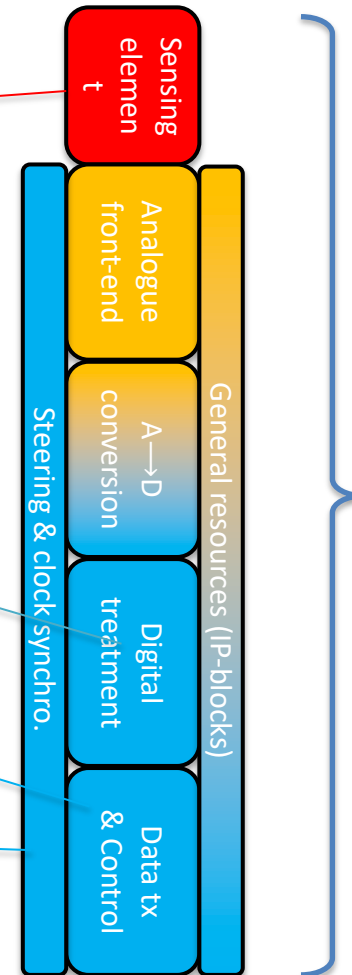
- Explore asynchronous logic (entirely event driven)
- Increase versatility (hit-rate, area), decrease power

■ Intelligence on sensor

- Embedded processor and artificial intelligence
- Data reduction, ease control/calibration against granularity curse

■ Functional blocks

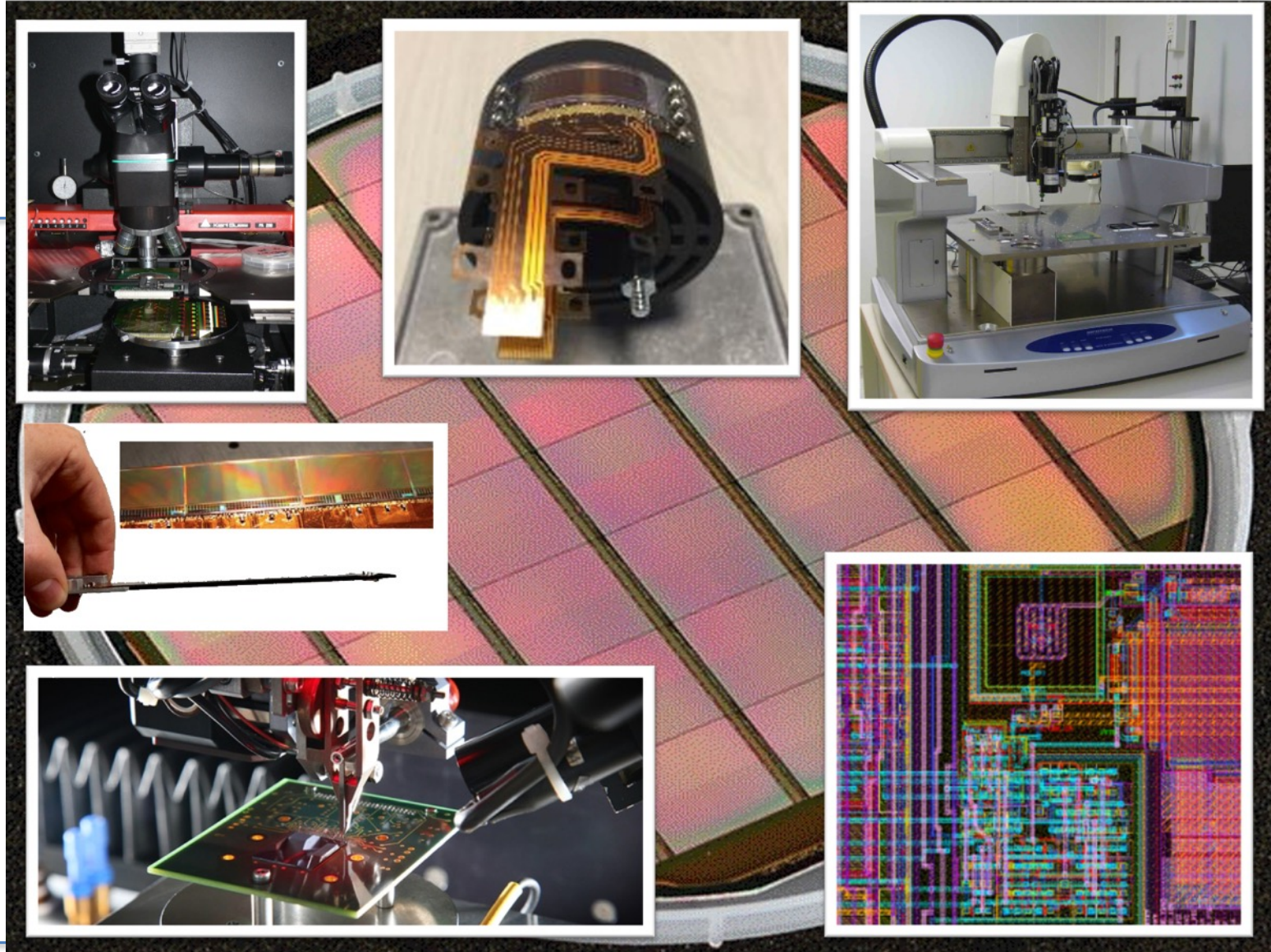
■ Sensor Bending



Main activity at C4Pi generated by scientific group requests

Let's listen to their programs

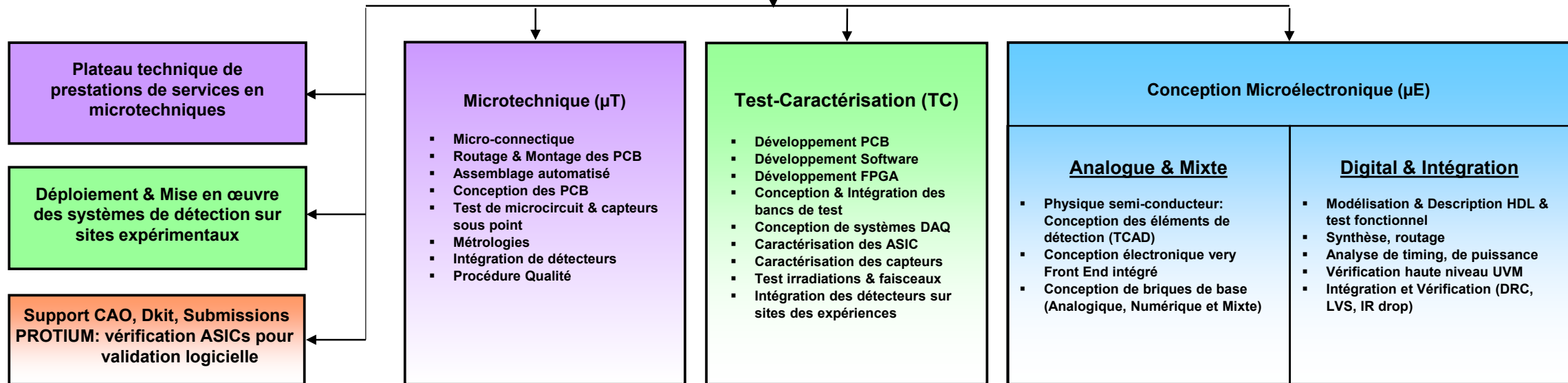
Supplementary slides



Comité de Pilotage

Direction de la Plateforme C4Pi

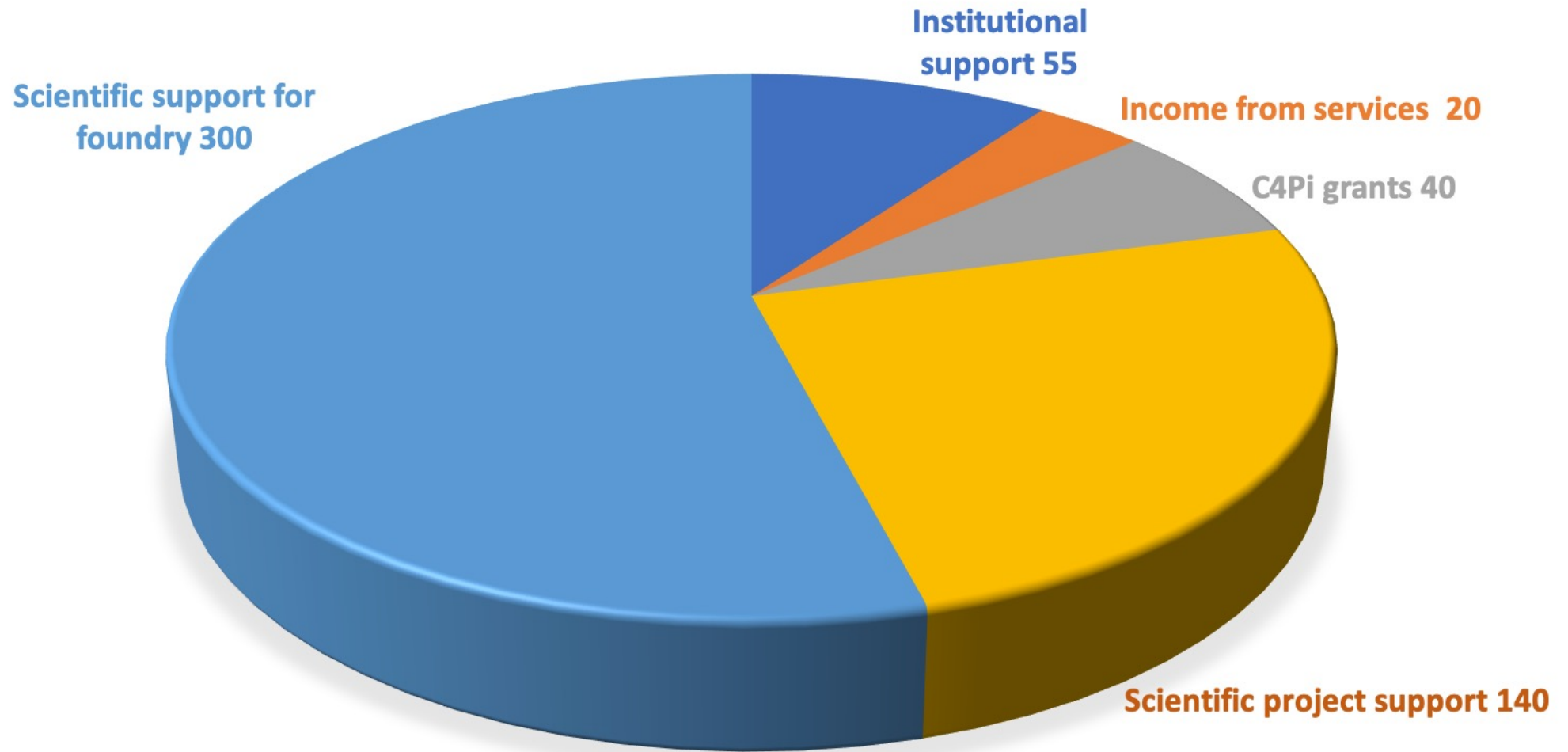
Responsable Opérationnelle (RO)
Coordinateur Scientifique (CS)
Responsable Opérationnelle Adjoint (ROJ)
Responsable Qualité (RQ)



Collaborations nationales & internationales, Groupes scientifiques & Supports de l'IPHC (RH, Finances, STI, ...)

2023

Average yearly budget (k€)

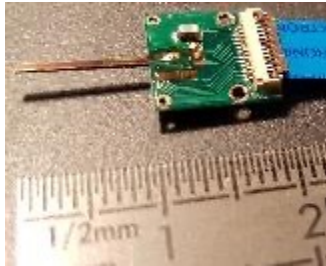


Note: Services, grants, foundry fluctuate

“Other” projects, aside collider physics

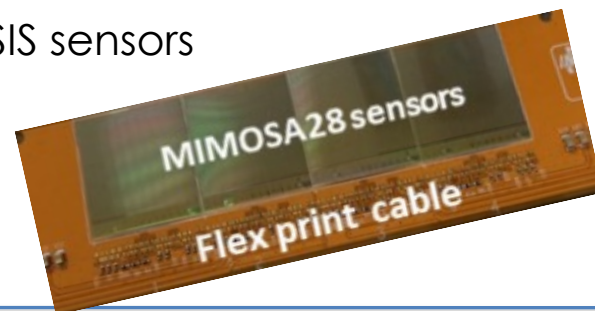
■ MAPSSIC

- Intracerebral β^+ probe for awake and free rodents
- Collab. CPPM, IJClab, IPHC, CERMEP
- Design of needle-shape sensor + Probe assembly



■ FOOT

- Doubly-differential nuclear cross-sections for hadrontherapy
- Collab. INFN-LNF, IPHC-DeSIS,
- Provider of MIMOSA-28 / MIMOSIS sensors
- Assembly of tracker
 - Light double-sided 8x8 cm² plane



■ STRONG, TIIMM / TIIX

- Tracking and Ion identification with minimal material budget
- Collab. GSI, INFN-LNF, IPHC, IP2I
- Design of TIIM and TIIX demonstrator sensors
 - E_{loss} dynamic: 5 keV to 5 MeV
 - In-pixel digitisation with Time-over-Threshold technique

■ Monolithic Imager

- All-purpose analogue-output sensor with 20 μm pixels
- => Proton spectroscopy for diagnostic of ion acceleration in plasma (with LP2I)
- => Electron/proton separation in space radiation (with Weeroc & CNES)
- => X-ray spectroscopy (with TÜB)

Large CMOS Monolithic Active Pixel Sensors

Sensor	MIMOSA26/28	ALPIDE	MIMOSIS-2	TJ-MONOPIX2	MALTA-2	LF-MONOPIX2	ARCADIA MD2	ATLASPix-3	MuPix10
Date	2008/10	2015-17	2023	2021	2021	2021	2021	2019	2020
Labo/Collab	IPHC	CERN+	IPHC	CERN-Bonn+	CERN+	Bonn-CERN+	INFN	KIT+	KIT+
Techno	AMS-350 nm	TJ-180 nm	TJ-180 nm	TJ-180 nm	TJ-180 nm	LF-150 nm	LF-110 nm	TSI 180 nm	TSI 180 nm
Pixel pitch (μm^2)	18.4x18.4 20.7x20.7	29x27	30x27	33x33	36.4x36.4	150x50	25x25	150x50	80x81
#Columns x #Rows	1152x576 960/928	1024x512	1024x504	512x512	256x512	56x340	512x512	132x372	256x250
Sensitive area (mm^2)	21.2x10.6 19.7x19.2	27.5x15.0	31.0x13.6	16.9x16.9	10x20	8.4x17	12.8x12.8	19.8x18.6	20.5x20.0
Time Stamp (ns)	112/ $\times 10^3$	5000	5000	25	25	25	?	25	20
Trigger latency (μs)	Continuous r.o.	Contin./Trig. 2	Continuous	Global shutter	Global shutter	Continuous	?	25	?
Output charge (bits)	1	1	1	7		6	?	7	5
Bandwidth (Mbits/s)	180	1200	3200	320	1300		2000	1300	?
Power (mW/cm^2)	300/150	18-35	~50	O(200)	>70		O(20) ?	150	4.6 $\mu\text{W}/\text{pixel}$
Hit rate (Mhz/cm^2)	O(0.1)	<10	15-70	>100	>100	>100	>100	>100	?
TID kGy	2	27	100	1000	1000		?	1000	?
Fluence ($\times 10^{13} n_{\text{eq}} \cdot \text{cm}^{-2}$)	0.1	1.7	10	300	300	100	?	100	100